

Appln. No. 10/519,895  
Amendment dated: 1/8/2007  
Reply to Office Action of July 7, 2006

**AMENDMENTS TO THE CLAIMS:**

Please amend the claims as follows:

1. (Currently Amended) A magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields,

wherein a magnetic shield layer made from a soft magnetic metal is formed at a top and a bottom region of said device for suppressing penetration of magnetic flux into said device,

wherein said magnetic shield layers are formed at the mounting side of said device, and on a device surface opposite to said mounting side of said device, and

wherein said device includes a plurality of layers between the magnetic shield layers, at least one of said plurality of layers and at least one of said magnetic shield layers having a same material.

Claim 2. (Cancelled)

3. (Currently Amended) The magnetic non-volatile memory device according to claim 1, said device ~~characterized in that~~ wherein:

said magnetic shield layer is formed of a nano granular structure having a magnetic layer and a non-magnetic layer.

4. (Currently Amended) The magnetic non-volatile memory device according to claim 1, said device ~~characterized in that~~ wherein:

said magnetic shield layer has a composing element which is common to a part of an element of various layers composing said device.

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5. (Currently Amended) The magnetic non-volatile memory device according to claim 1, ~~said device characterized in that~~ wherein:

a passivation film is formed on said magnetic shield layer.

6. (Currently Amended) The magnetic non-volatile memory device according to claim 1, ~~said device characterized in that~~ wherein:

said magnetic shield layers formed on a device surface at the mounting side of said device, and a device surface opposite to said mounting side of said device, are magnetically coupled with each other.

7. (Currently Amended) The magnetic non-volatile memory device according to claim 4, ~~said device characterized in that~~ wherein:

said composing element includes one selected from the group consisting of Fe, Co, Pt, Mn, and Al.

8. (Currently Amended) A method for manufacturing a magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields, said method ~~characterized in that~~ comprising the steps of:

~~various layers formed in~~ forming a layer of said device and a magnetic shield layer ~~formed at top and bottom regions of said device~~ for suppressing penetration of magnetic flux into said device ~~are formed in a single sputtering chamber; and~~

using a single target used in for forming at least one of the shield layers is the same as a target and for forming a layer of said device located between the magnetic

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shield layers.

9. (New) A magnetic non-volatile memory device provided with a magnetic shielding structure for suppressing the influence of external magnetic fields,

wherein a magnetic shield layer made from a soft magnetic metal is formed at a top and a bottom region of said device for suppressing penetration of magnetic flux into said device,

wherein said magnetic shield layers are formed at the mounting side of said device, and on a device surface opposite to said mounting side of said device,

wherein said device includes a plurality of layers between the magnetic shield layers, at least one of said plurality of layers and at least one of said magnetic shield layers having a same material; and

wherein a plurality of said non-volatile memory devices are arranged in an array and at least one of said magnetic shield layers extends across substantially the entire array of memory devices.

10. (New) A magnetic non-volatile memory device as defined in claim 9, wherein said magnetic shield layer is formed of a nano-granular structure having a magnetic and a non-magnetic layer.

11. (New) A magnetic non-volatile memory device as defined in claim 9, further including a passivation film on said second magnetic shield layer.

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12. (New) A wafer including a plurality of magnetic non-volatile memory devices said wafer comprising:

a plurality of information storage sections attached to a substrate, each said information storage section including a plurality of layers;

a first magnetic shield layer for suppressing the influence of external magnetic fields, said first magnetic shield layer formed across substantially the entire substrate;

a second magnetic shield layer for suppressing the influence of external magnetic fields, said second magnetic shield layer formed at a side of said plurality of information storage sections opposite said substrate; and

wherein at least one of said plurality of layers of said information storage sections and at least one of said magnetic shield layers have a same material.

13. A wafer as defined in claim 12, wherein said second magnetic shield layer extends across substantially the entire plurality of information storage sections.